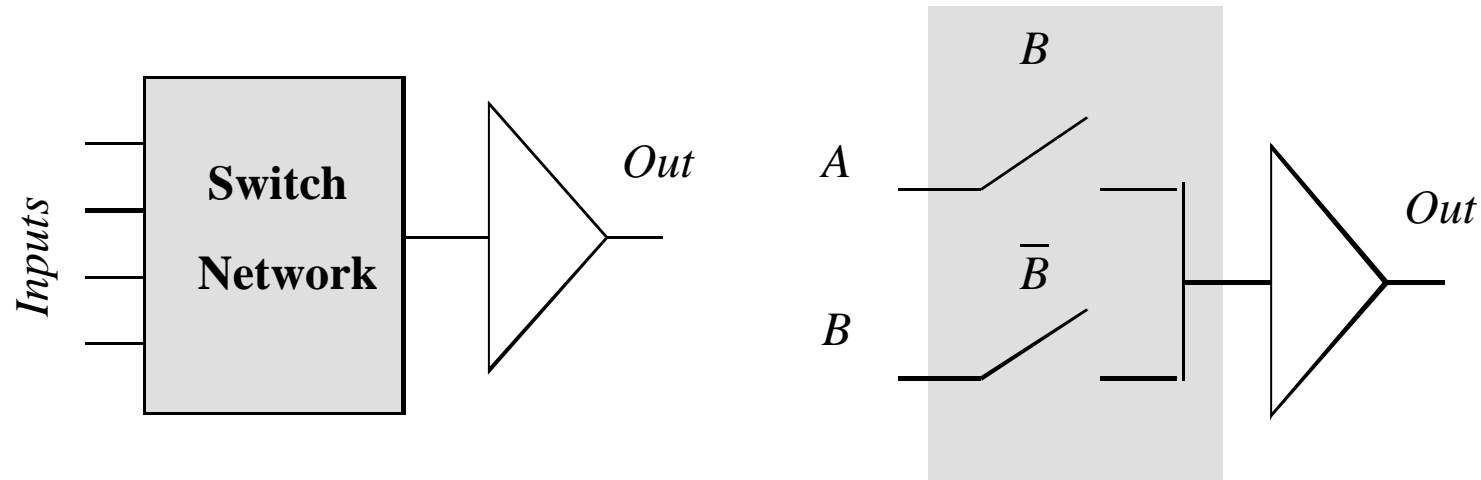




Pass-Transistor Logic

Pass-Transistor Logic



- **N transistors**
- **No static consumption**

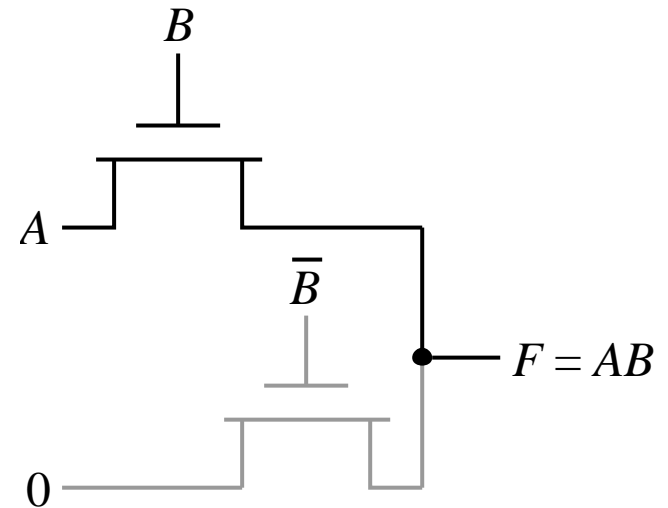
Primary inputs drive the gate terminals + source-drain terminals. In contrast to static CMOS – primary inputs drive gate terminals.

Example: AND Gate

When B is “1”, top device turns on and copies the input A to output F. When B is low, bottom device turns on and passes a “0”.

The presence of the switch driven by \bar{B} is essential to ensure that the gate is static – a low-impedance path must exist to supply rails.

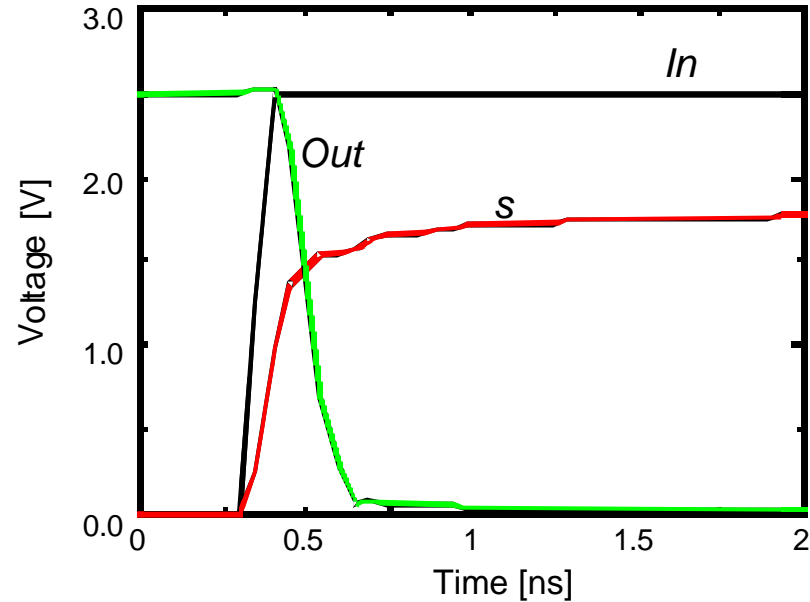
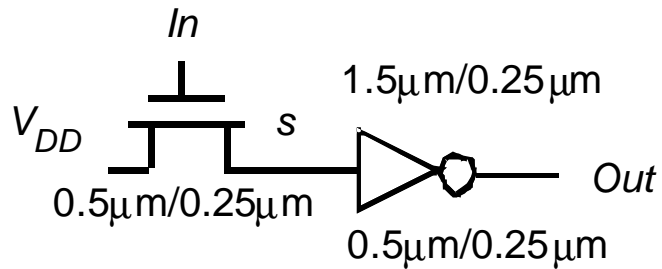
Adv.: Fewer devices to implement some functions.
Example: AND2 requires 4 devices (including inverter to invert B) vs. 6 for complementary CMOS (lower total capacitance).



NMOS is effective at passing a 0, but poor at pulling a node to V_{dd} . When the pass transistor a node high, the output only charges up to $V_{dd} - V_{tn}$. This becomes worse due to the body effect. The node will be charged up to $V_{dd} - V_{tn}(V_s)$

$$V_s = V_{dd} - (V_{tn0} + g(\sqrt{|2\Phi_f| + V_s} - \sqrt{|2\Phi_f|}))$$

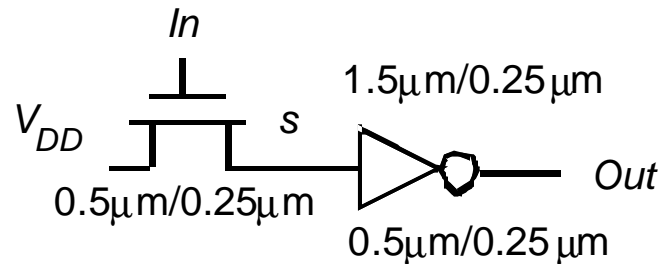
NMOS-Only Logic



V_s is initially 0. V_s will initially charge up quickly, but the tail end of the transient is slow. The current drive of the transistor (gate-to-source voltage) is reduced significantly as V_s approaches $V_{dd} - V_{tn}$ (the current available to charge up node "s" is reduced drastically).

For cascading, the output of a pass transistor (#1) should not drive the gate of another MOS device (#2). This will produce an output = $V_{dd} - V_{tn1} - V_{tn2}$

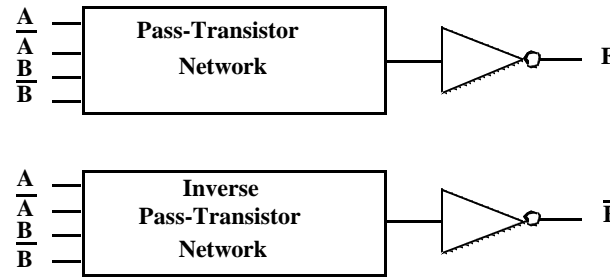
Energy Consumption



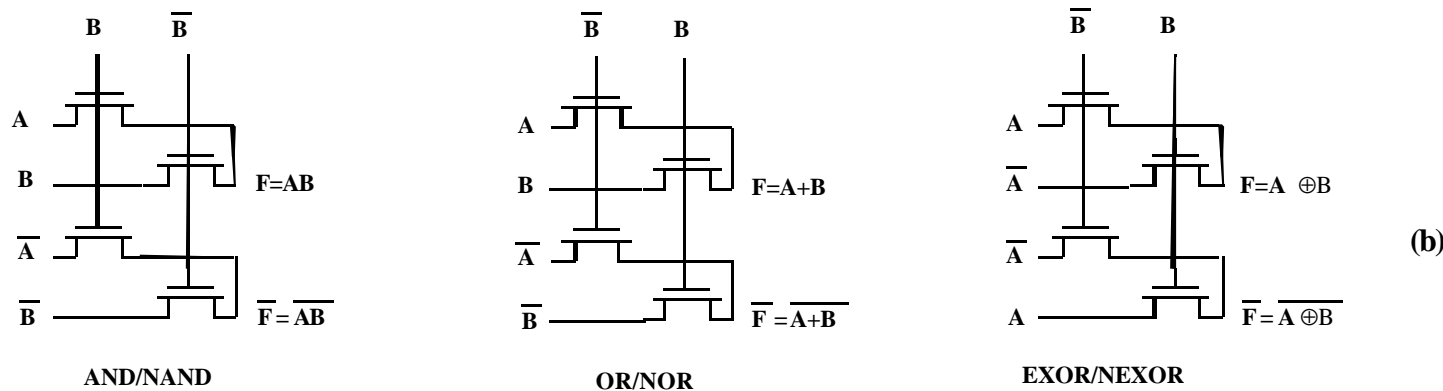
Pass transistors require lower switching energy to charge up a node, due to the reduced voltage swing. The output node charges from $0 \rightarrow V_{dd} - V_{tn}$, and the energy drawn from the power supply for charging the output of a pass transistor is given by $C_L \cdot V_{dd} (V_{dd} - V_{tn})$

While lower switching power is consumed, it may consume **static power** when output is high – the reduced voltage level may be insufficient to turn off the PMOS transistor of the subsequent CMOS inverter.

Complementary Pass Transistor Logic

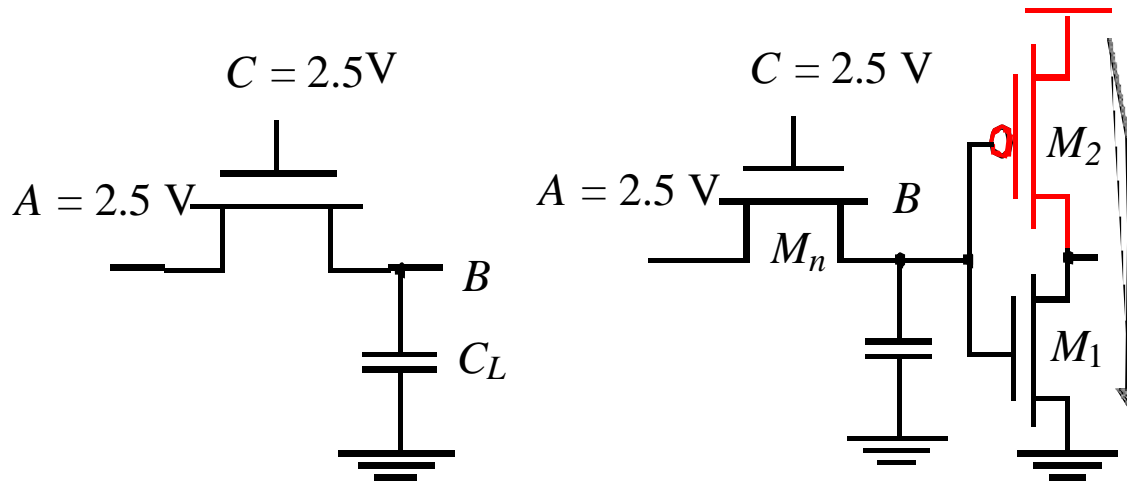


(a) **To accept and produce true and complementary inputs and outputs.**



- Since circuit is differential, complimentary inputs and outputs are available. Although generating differential signals require extra circuitry, complex gates such as XORs, MUXs and adders can be realized efficiently.
- CPL is a static gate, because outputs are connected to Vdd or GND through a low-resistance path (high noise resilience).
- Design is modular – all gates use same topology; only inputs are permuted. This facilitates the design of a library of gates.

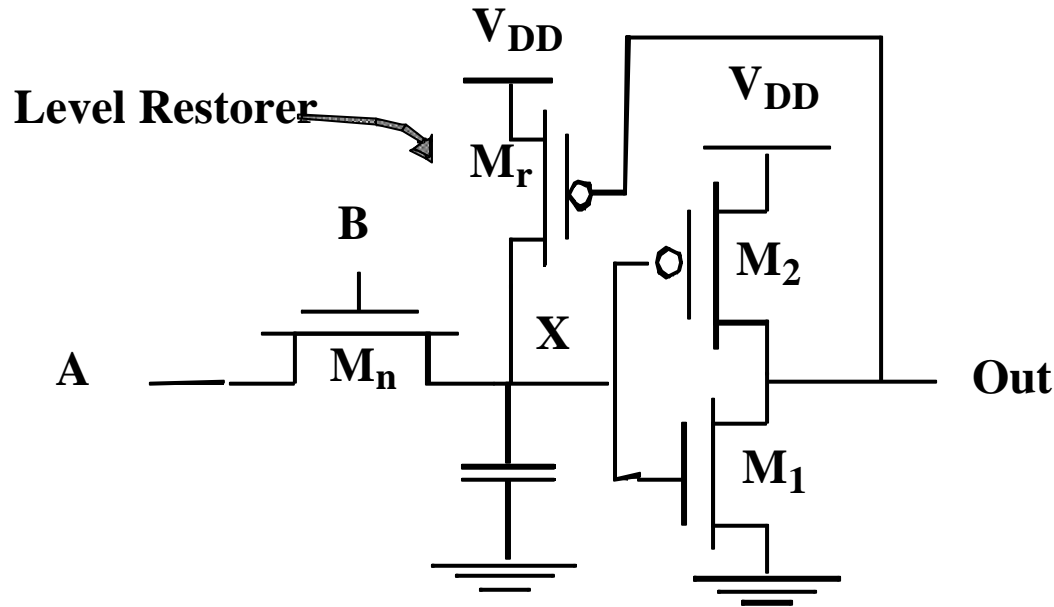
Main Problems of NMOS-only Switch



V_B does not pull up to 2.5V, but $2.5V - V_{TN}$

**Threshold voltage loss causes
static power consumption + slower transition**

NMOS Only Logic: Level Restoring Transistor

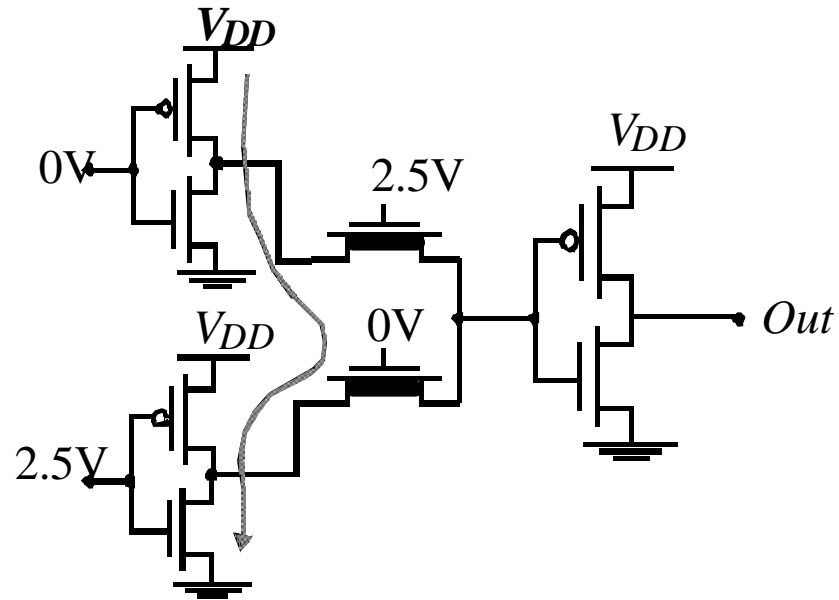


- Advantage: Full Swing. Eliminates static power in inverter + static power through level restorer and pass transistor, since restorer is only active when A is high.
- Restorer adds capacitance, takes away pull down current at X – contention between M_n and M_r (slower switching). Hence M_r must be sized small. M_n and M_r must be sized such that the voltage at node X drops below the threshold of the inverter V_{M} , which is a function in the sizes of M_1 and M_2 .

Solution 2: Single Transistor Pass Gate with $V_T \sim 0$

Use very low threshold values for NMOS pass transistors, and standard high-threshold devices for inverters.

Note: Body effect will still cause an increase in the threshold voltage.



**WATCH OUT FOR LEAKAGE CURRENTS
(DC Sneak path)**

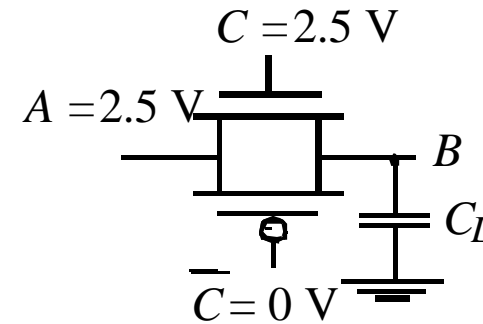
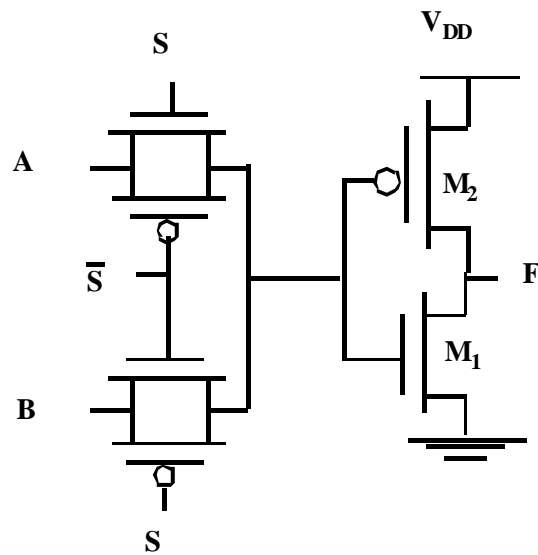
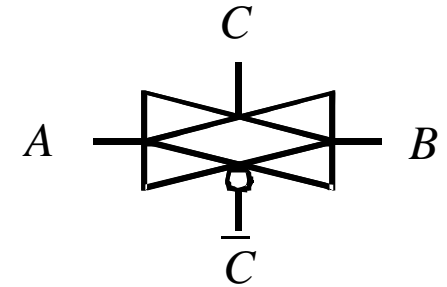
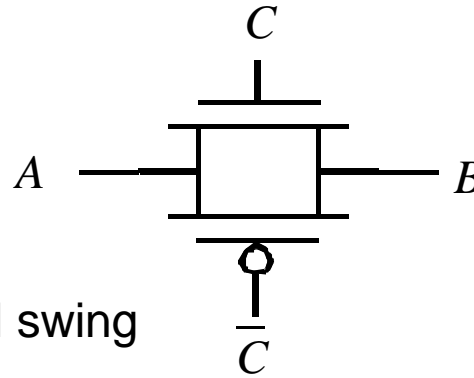
While these leakage paths are not critical when the device is switching constantly, they do pose a large energy overhead when the circuit is in the ideal state.

Solution 3: Transmission Gate

NMOS passes a strong "0"
PMOS passes a strong "1"

Transmission gates enable rail-to-rail swing

These gates are particularly efficient in implementing MUXs



$$\overline{F} = (\overline{A}S + B\overline{S})$$

6 devices vs. 8 for complementary CMOS

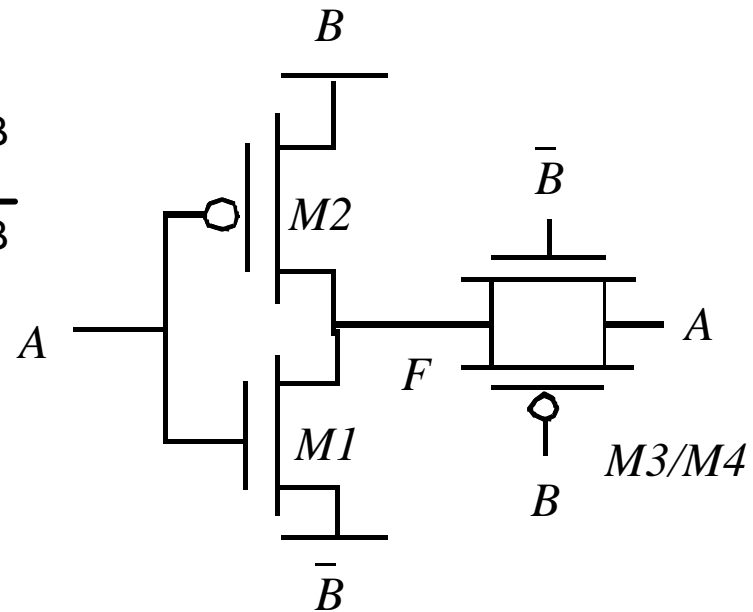
Another Example: Transmission Gate XOR

6 devices (including inverter for B) vs. 12 for complementary CMOS

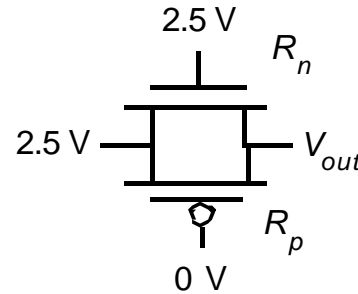
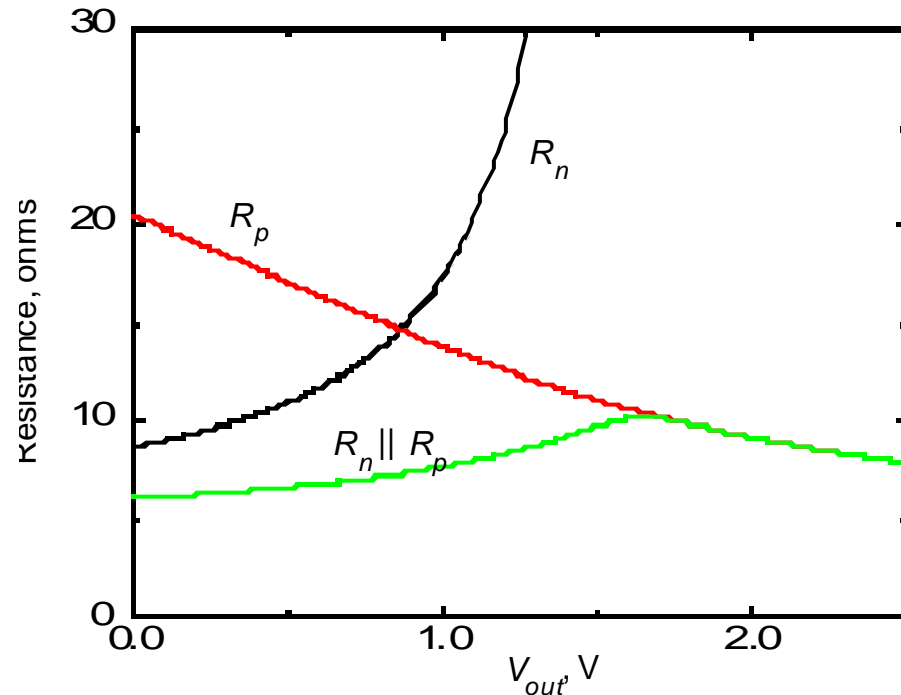
For B=1, M3 & M4 are off, M1 & M2 are on. $F = \overline{AB}$

For B=0, M1 & M2 are off. M3 & M4 are on. $F = \overline{AB}$

Regardless of the value of A & B, node F is connected to V_{dd} or GND (static gate)

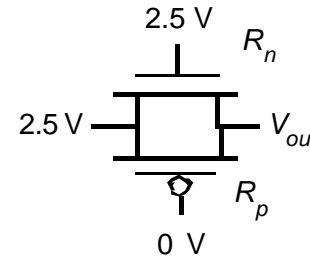
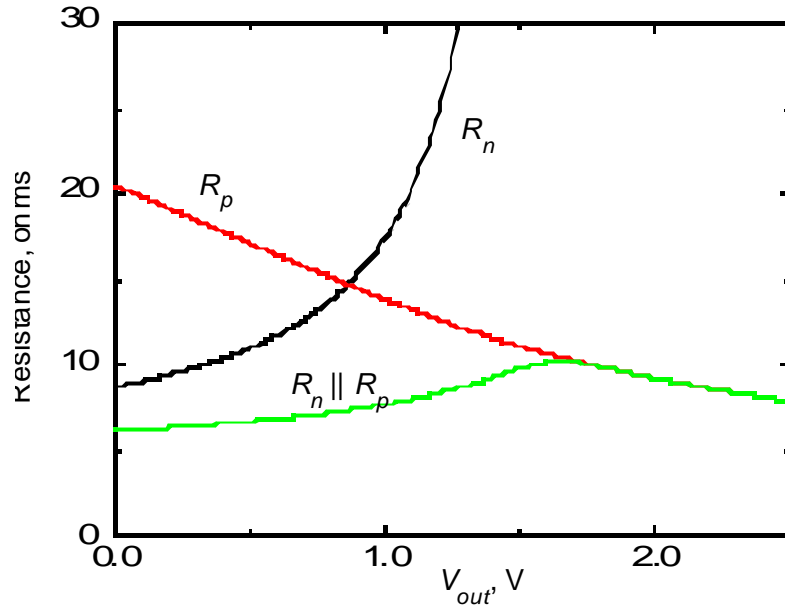


Resistance of Transmission Gate



$R_n \{(V_{dd}-V_{out})/I_n\}$ & $R_p \{(V_{dd}-V_{out})/I_p\}$ are in parallel. The currents through devices are dependent on value of V_{out} and hence the operating mode of the transistors. During the low-to-high transition, the pass transistors traverse through a number of operation modes.

Since V_d and $V_g = V_{dd}$, the NMOS is either in saturation or off. The PMOS changes from saturation to linear during the transient.



- $V_{out} < |V_{tp}|$: NMOS and PMOS saturated
- $|V_{tp}| < V_{out} < V_{dd} - V_{tn}$: NMOS saturated, PMOS linear
- $V_{dd} - V_{tn} < V_{out}$: NMOS cutoff, PMOS linear

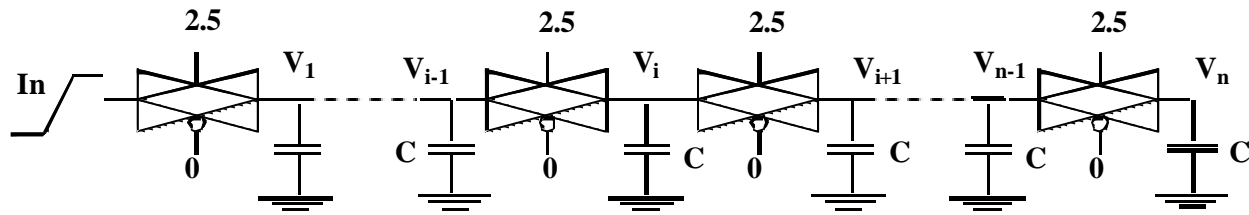
R_{eq} is relatively constant. Thus when analyzing transmission-gate networks, the simplifying assumption that the switch has a constant resistive value is acceptable.

$$R_n = \frac{V_{dd} - V_{out}}{I_n} = \frac{V_{dd} - V_{out}}{k_n \left[(V_{dd} - V_{tn})(V_{dd} - V_{out}) - \frac{(V_{dd} - V_{out})^2}{2} \right]} \approx \frac{1}{k_n (V_{dd} - V_{tn})}$$

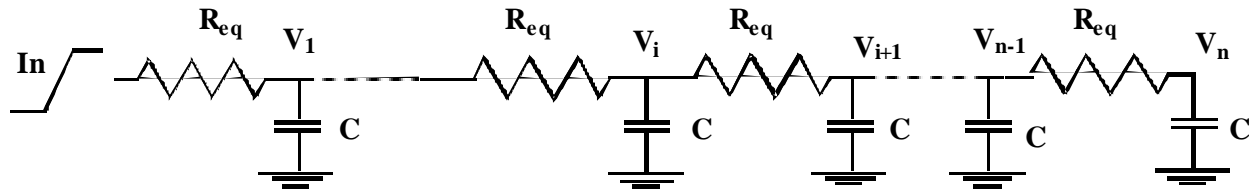
Similarly,

$$R_p = \frac{V_{dd} - V_{out}}{I_p} \approx \frac{1}{k_p (V_{dd} - |V_{tp}|)}$$

Delay in Transmission Gate Networks



(a)



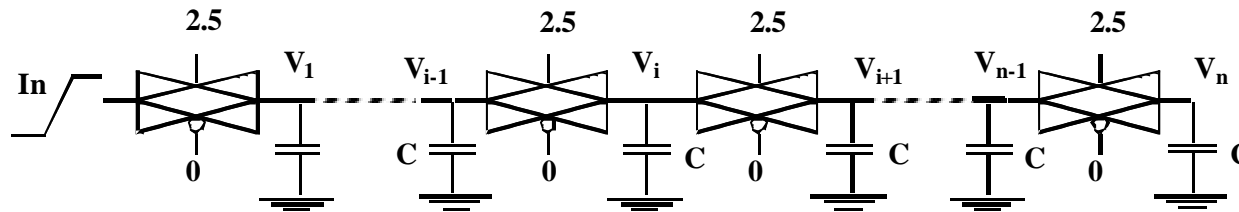
(b)

$$t_p = 0.69 \sum_{k=0}^n CR_{eq} k = 0.69 CR_{eq} \frac{n(n+1)}{2}$$

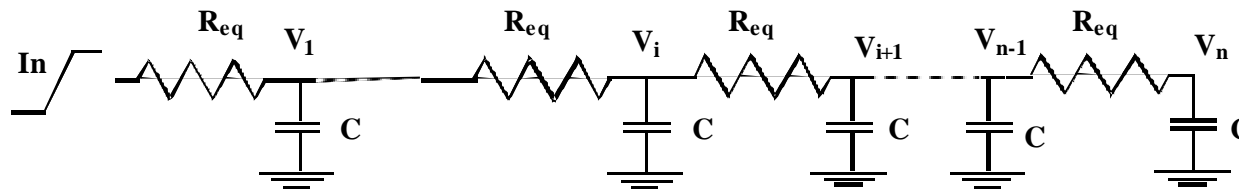
t_p is proportional to n^2 and increases rapidly with the number of switches in the chain.

Solution: Insert buffers.

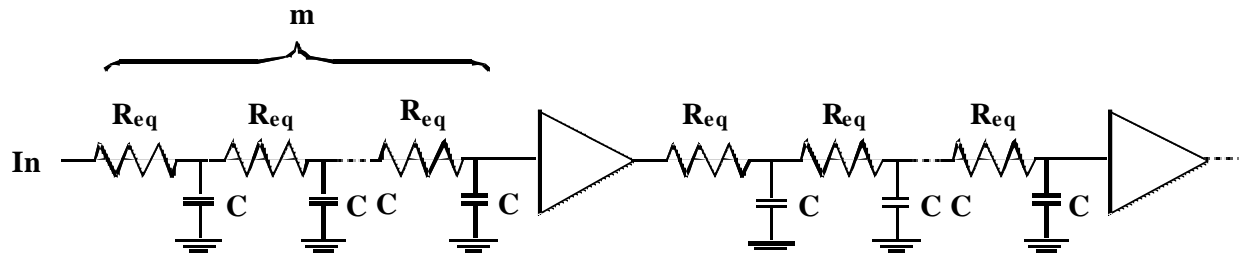
Delay Optimization



(a)



(b)



(c)

$$t_p = 0.69 \left[\frac{n}{m} CR_{eq} \frac{m(m+1)}{2} \right] + \left(\frac{n}{m} - 1 \right) t_{buf}$$

Linear dependence on n instead of n^2

To find m_{opt} then $\frac{\partial t_p}{\partial m} = 0$ yielding $m_{opt} = 1.7 \sqrt{\frac{t_{buf}}{CR_{eq}}}$